

**MOTOROLA  
SEMICONDUCTOR  
TECHNICAL DATA**

**MC4558,  
MC4558AC  
MC4558C**

**2**

**Dual Wide Bandwidth  
Operational Amplifier**

The MC4558, AC, and C combine all the outstanding features of the MC1458 and, in addition, possess three times the unity gain bandwidth of the industry standard.

- 2.5 MHz Unity Gain Bandwidth Guaranteed (MC4558 and MC4558AC)
- 2.0 MHz Unity Gain Bandwidth Guaranteed (MC4558C)
- Internally Compensated
- Short Circuit Protection
- Gain and Phase Match between Amplifiers
- Low Power Consumption

**MAXIMUM RATINGS** (T<sub>A</sub> = +25°C, unless otherwise noted.)

Rating	Symbol	MC4558 MC4558AC	MC4558C	Unit
Power Supply Voltage	V <sub>CC</sub> V <sub>EE</sub>	+22 -22	+18 -18	Vdc
Input Differential Voltage	V <sub>ID</sub>	±30		V
Input Common Mode Voltage (Note 1)	V <sub>ICM</sub>	±15		V
Output Short Circuit Duration (Note 2)	t <sub>SC</sub>	Continuous		
Ambient Temperature Range	T <sub>A</sub>	-55 to +125 0 to +70		
Storage Temperature Range	T <sub>stg</sub>	-65 to +150 -55 to +125		°C
Junction Temperature	T <sub>J</sub>	175 150		°C

- NOTES:**
1. For supply voltages less than ±15 V, the absolute maximum input voltage is equal to the supply voltage
  2. Short circuit may be to ground or either supply.

**DUAL WIDE BANDWIDTH  
OPERATIONAL AMPLIFIER**

**SILICON MONOLITHIC  
INTEGRATED CIRCUIT**



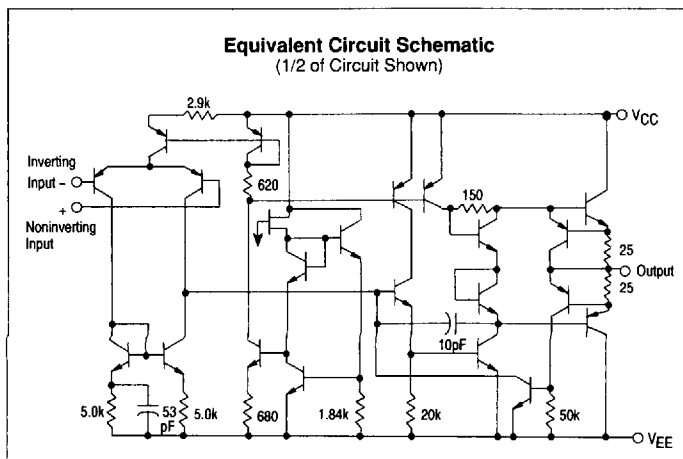
**P1 SUFFIX  
PLASTIC PACKAGE  
CASE 626**



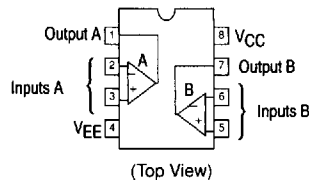
**U SUFFIX  
CERAMIC PACKAGE  
CASE 693**



**D SUFFIX  
PLASTIC PACKAGE  
CASE 751  
(SO-8)**



**PIN CONNECTIONS**



**ORDERING INFORMATION**

Device	Temperature Range	Package
MC4558U	-55° to +125°C	Ceramic DIP
MC4558CD		SO-8
MC4558ACP1, CP1	0° to +70°C	Plastic DIP
MC4558CU		Ceramic DIP

## MC4558, MC4558AC, MC4558C

FREQUENCY CHARACTERISTICS ( $V_{CC} = +15\text{ V}$ ,  $V_{EE} = -15\text{ V}$ ,  $T_A = 25^\circ\text{C}$ )

Characteristics	Symbol	MC4558, MC4558AC			MC4558C			Unit
		Min	Typ	Max	Min	Typ	Max	
Unity Gain Bandwidth	BW	2.5	2.8	—	2.0	2.8	—	MHz

ELECTRICAL CHARACTERISTICS ( $V_{CC} = 15\text{ V}$ ,  $V_{EE} = -15\text{ V}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise noted.)

Input Offset Voltage ( $R_S \leq 10\text{ k}\Omega$ )	$V_{IO}$	—	1.0	5.0	—	2.0	6.0	mV
Input Offset Current	$I_{IO}$	—	20	200	—	20	200	nA
Input Bias Current (Note 1)	$I_{IB}$	—	80	500	—	80	500	nA
Input Resistance	$r_i$	0.3	2.0	—	0.3	2.0	—	$M\Omega$
Input Capacitance	$C_i$	—	1.4	—	—	1.4	—	pF
Common Mode Input Voltage Range	$V_{ICR}$	$\pm 12$	$\pm 13$	—	$\pm 12$	$\pm 13$	—	V
Large Signal Voltage Gain ( $V_O = \pm 10\text{ V}$ , $R_L = 2.0\text{ k}\Omega$ )	$AV_{OL}$	50	200	—	20	200	—	V/mV
Output Resistance	$r_o$	—	75	—	—	75	—	$\Omega$
Common Mode Rejection ( $R_S \leq 10\text{ k}\Omega$ )	CMR	70	90	—	70	90	—	dB
Supply Voltage Rejection Ratio ( $R_S \leq 10\text{ k}\Omega$ )	PSRR	—	30	150	—	30	150	$\mu\text{V/V}$
Output Voltage Swing ( $R_L \geq 10\text{ k}\Omega$ ) ( $R_L \geq 2.0\text{ k}\Omega$ )	$V_O$	$\pm 12$ $\pm 10$	$\pm 14$ $\pm 13$	—	$\pm 12$ $\pm 10$	$\pm 14$ $\pm 13$	—	V
Output Short Circuit Current	$I_{SC}$	10	20	40	10	20	40	mA
Supply Currents (Both Amplifiers)	$I_D$	—	2.3	5.0	—	2.3	5.6	mA
Power Consumption (Both Amplifiers)	$P_C$	—	70	150	—	70	170	mW
Transient Response (Unity Gain) ( $V_i = 20\text{ mV}$ , $R_L \geq 2.0\text{ k}\Omega$ , $C_L \leq 100\text{ pF}$ ) Rise Time ( $V_i = 20\text{ mV}$ , $R_L \geq 2.0\text{ k}\Omega$ , $C_L \leq 100\text{ pF}$ ) Overshoot ( $V_i = 10\text{ V}$ , $R_L \geq 2.0\text{ k}\Omega$ , $C_L \leq 100\text{ pF}$ ) Slew Rate	$t_{TLH}$ $t_{os}$ SR	— — 1.5	0.3 15 1.6	— — —	— — 1.0	0.3 15 1.6	— — —	$\mu\text{s}$ % V/ $\mu\text{s}$

ELECTRICAL CHARACTERISTICS ( $V_{CC} = +15\text{ V}$ ,  $V_{EE} = -15\text{ V}$ ,  $T_A = T_{high}$  to  $T_{low}$ , unless otherwise noted. See Note 2.)

Input Offset Voltage ( $R_S \leq 10\text{ k}\Omega$ )	$V_{IO}$	—	1.0	6.0	—	—	7.5	mV
Input Offset Current ( $T_A = T_{high}$ ) ( $T_A = T_{low}$ ) ( $T_A = 0^\circ$ to $+70^\circ\text{C}$ )	$I_{IO}$	— — —	7.0 85 —	200 500 —	— — —	— — —	300	nA
Input Bias Current ( $T_A = T_{high}$ ) ( $T_A = T_{low}$ ) ( $T_A = 0^\circ$ to $+70^\circ\text{C}$ )	$I_{IB}$	— — —	30 300 —	500 1500 —	— — —	— — —	800	nA
Common Mode Input Voltage Range	$V_{ICR}$	$\pm 12$	$\pm 13$	—	—	—	—	V
Large Signal Voltage Gain ( $V_O = \pm 10\text{ V}$ , $R_L = 2.0\text{ k}\Omega$ )	$AV_{OL}$	25	—	—	15	—	—	V/mV
Common Mode Rejection ( $R_S \leq 10\text{ k}\Omega$ )	CMR	70	90	—	—	—	—	dB
Supply Voltage Rejection Ratio ( $R_S \leq 10\text{ k}\Omega$ )	PSRR	—	30	150	—	—	—	$\mu\text{V/V}$
Output Voltage Swing ( $R_L \geq 10\text{ k}\Omega$ ) ( $R_L \geq 2.0\text{ k}\Omega$ )	$V_O$	$\pm 12$ $\pm 10$	$\pm 14$ $\pm 13$	—	$\pm 12$ $\pm 10$	$\pm 14$ $\pm 13$	—	V
Supply Currents (Both Amplifiers) ( $T_A = T_{high}$ ) ( $T_A = T_{low}$ )	$I_D$	— —	— —	4.5 6.0	— —	— —	5.0 6.7	mA
Power Consumption (Both Amplifiers) ( $T_A = T_{high}$ ) ( $T_A = T_{low}$ )	$P_C$	— —	— —	135 180	— —	— —	150 200	mW

NOTES: 1.  $I_{IB}$  is out of the amplifier due to PNP input transistors.

2.  $T_{high} = +125^\circ\text{C}$  for MC4558

$T_{low} = -55^\circ\text{C}$  for MC4558

$= +70^\circ\text{C}$  for MC4558C and MC4558AC

$= 0^\circ\text{C}$  for MC4558C and MC4558AC.

MC4558, MC4558AC, MC4558C

Figure 1. Burst Noise versus Source Resistance

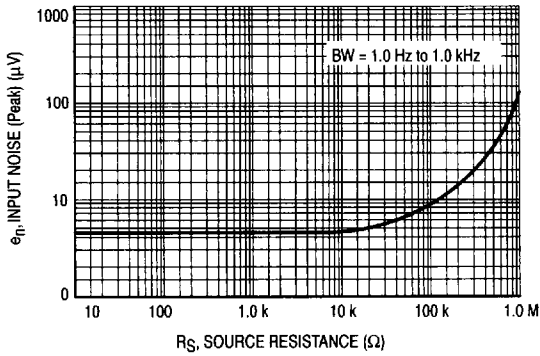


Figure 2. RMS Noise versus Source Resistance

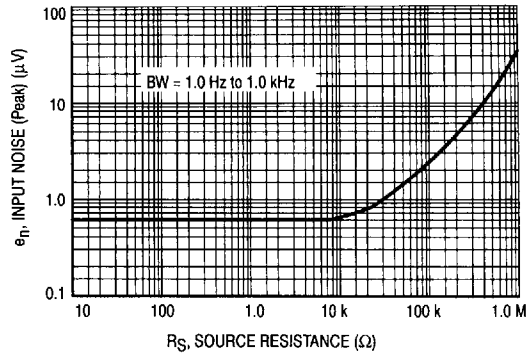


Figure 3. Output Noise versus Source Resistance

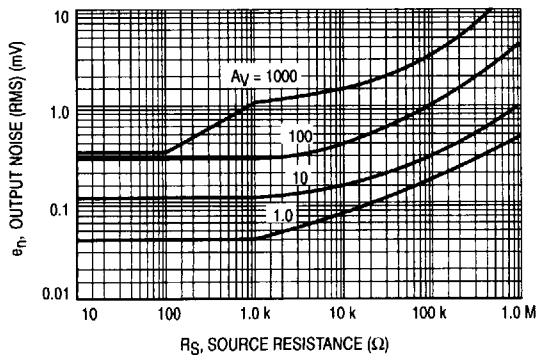


Figure 4. Spectral Noise Density

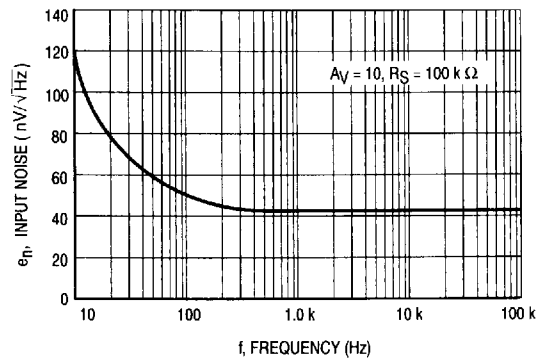
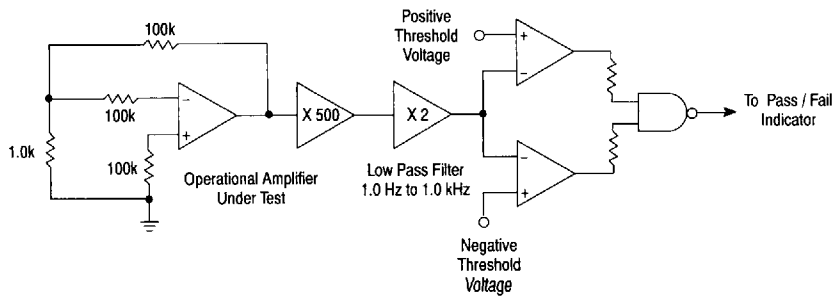


Figure 5. Burst Noise Test Circuit



Unlike conventional peak reading or RMS meters, this system was especially designed to provide the quick response time essential to burst (popcorn) noise testing.

The test time employed is 10 sec and the 20 μV peak limit refers to the operational amplifier input thus eliminating errors in the closed-loop gain factor of the operational amplifier.

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Figure 6. Open-Loop Frequency Response

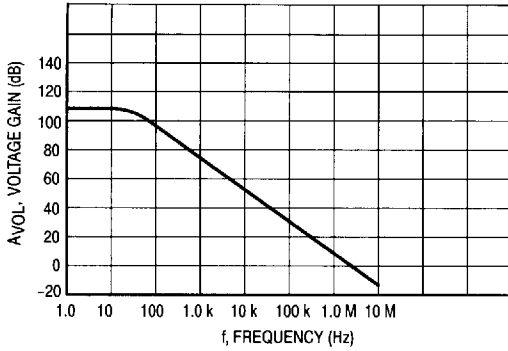


Figure 7. Phase Margin versus Frequency

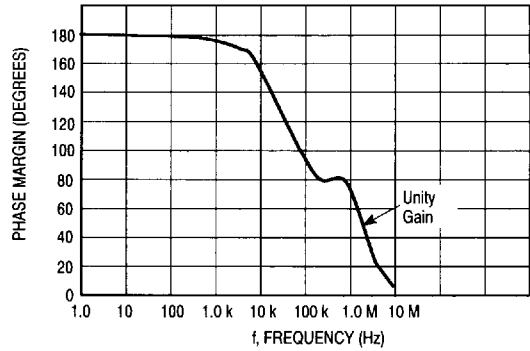


Figure 8. Positive Output Voltage Swing versus Load Resistance

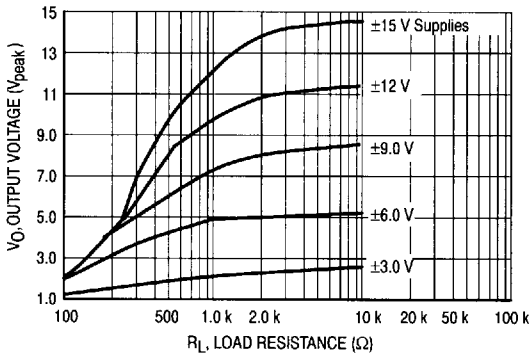


Figure 9. Negative Output Voltage Swing versus Load Resistance

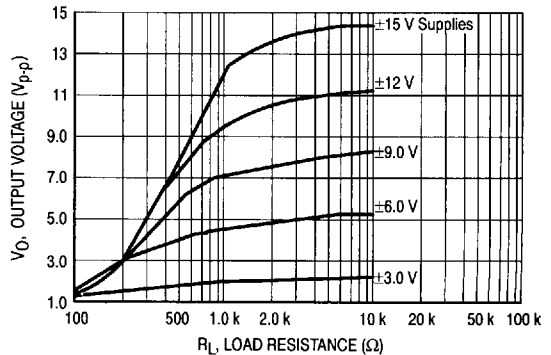


Figure 10. Power Bandwidth (Large Signal Swing versus Frequency)

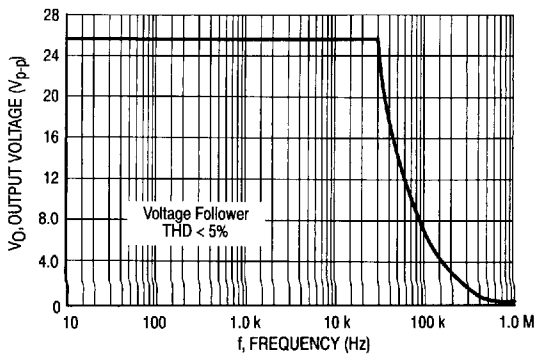


Figure 11. Transient Response Test Circuit

